

**P-Channel Enhancement Mode Power MOSFET**

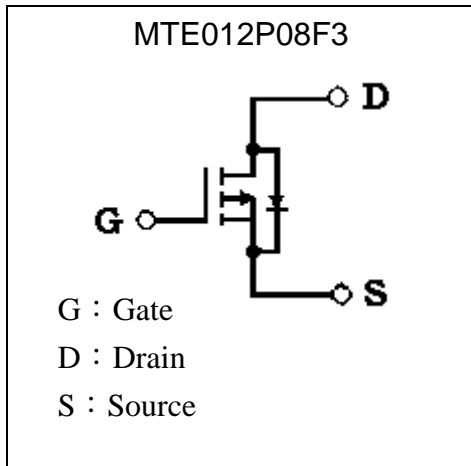
# MTE012P08F3

BV <sub>DSS</sub>	-80V
I <sub>D</sub> @ V <sub>GS</sub> =-10V, T <sub>C</sub> =25°C	-63A
I <sub>D</sub> @ V <sub>GS</sub> =-10V, T <sub>A</sub> =25°C	-8A
R <sub>DS(on)(TYP)</sub> @ V <sub>GS</sub> =-10V, I <sub>D</sub> =-50A	13.5mΩ

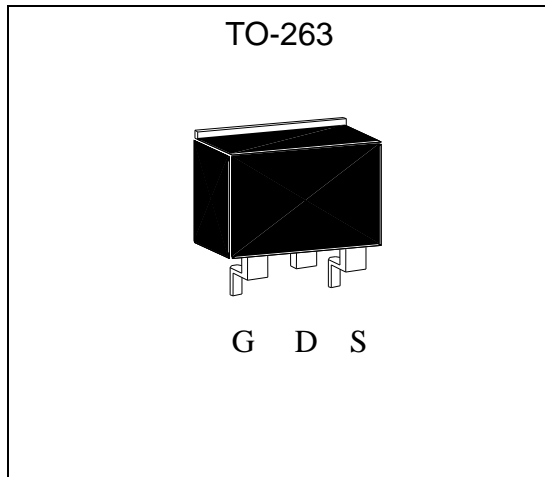
**Features**

- Low Gate Charge
- Simple Drive Requirement
- Repetitive Avalanche Rated
- Fast Switching Characteristic
- RoHS compliant package

**Symbol**

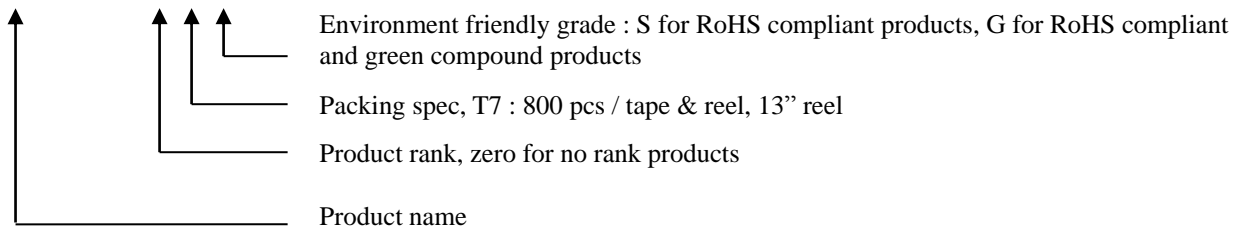


**Outline**



**Ordering Information**

Device	Package	Shipping
MTE012P08F3-0-T7-X	TO-263 (Pb-free lead plating and RoHS compliant package)	800 pcs / Tape & Reel



**Absolute Maximum Ratings** ( $T_C=25^{\circ}\text{C}$ , unless otherwise noted)

Parameter	Symbol	Limits	Unit	
Drain-Source Voltage	$V_{DS}$	-80	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current @ $T_C=25^{\circ}\text{C}$ , $V_{GS}=-10\text{V}$ (Note 5)	$I_D$	-63	A	
Continuous Drain Current @ $T_C=100^{\circ}\text{C}$ , $V_{GS}=-10\text{V}$ (Note 5)		-39.8		
Pulsed Drain Current (Note 3)	$I_{DM}$	-214		
Continuous Drain Current @ $T_A=25^{\circ}\text{C}$ , $V_{GS}=-10\text{V}$ (Note 2)	$I_{DSM}$	-8		
Continuous Drain Current @ $T_A=70^{\circ}\text{C}$ , $V_{GS}=-10\text{V}$ (Note 2)		-6.4		
Avalanche Current @ $L=0.1\text{mH}$ (Note 3)	$I_{AS}$	-90		
Avalanche Energy @ $L=1\text{mH}$ , $I_D=-40\text{A}$ , $V_{DD}=-25\text{V}$ (Note 4)	$E_{AS}$	800	mJ	
Repetitive Avalanche Energy	$E_{AR}$	12		
Power Dissipation	$P_D$	$T_C=25^{\circ}\text{C}$ (Note 1)	125	W
		$T_C=100^{\circ}\text{C}$ (Note 1)	50	
Power Dissipation	$P_{DSM}$	$T_A=25^{\circ}\text{C}$ (Note 2)	2	
		$T_A=70^{\circ}\text{C}$ (Note 2)	1.3	
Operating Junction and Storage Temperature	$T_j, T_{stg}$	-55~+150	$^{\circ}\text{C}$	

**Thermal Data**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{\theta JC}$	1	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-ambient, max, $t \leq 10\text{s}$ (Note 2)	$R_{\theta JA}$	15	
Thermal Resistance, Junction-to-ambient, max (Note 2)		62	

- Note : 1. The power dissipation  $P_D$  is based on  $T_{J(MAX)}=150^{\circ}\text{C}$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
2. The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2 oz. copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ . The power dissipation  $P_{DSM}$  is based on  $R_{\theta JA}$  and the maximum allowed junction temperature of  $150^{\circ}\text{C}$ . The value in any given application depends on the user's specific board design.
3. Pulse width limited by junction temperature  $T_{J(MAX)}=150^{\circ}\text{C}$ . Ratings are based on low frequency and low duty cycles to keep initial  $T_J=25^{\circ}\text{C}$ .
4. 100% tested by conditions of  $L=0.1\text{mH}$ ,  $I_{AS}=-30\text{A}$ ,  $V_{GS}=-10\text{V}$ ,  $V_{DD}=-25\text{V}$ .
5. Calculated continuous drain current based on maximum allowable junction temperature.
6. The static characteristics are obtained using  $<300\mu\text{s}$  pulses, duty cycle 0.5% maximum.
7. The  $R_{\theta JA}$  is the sum of thermal resistance from junction to case  $R_{\theta JC}$  and case to ambient.



**Characteristics (Tc=25°C, unless otherwise specified)**

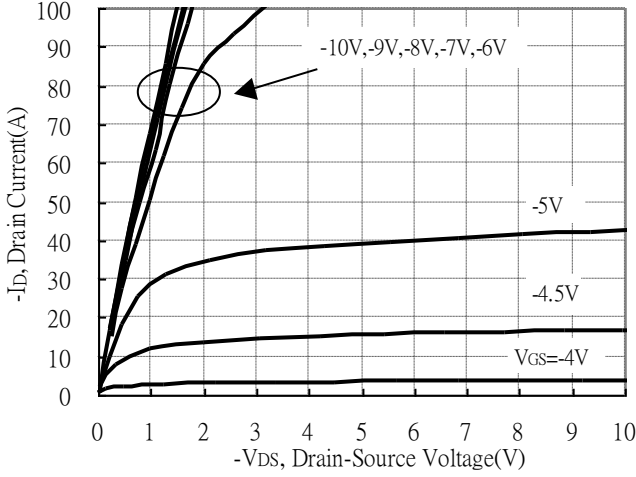
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
<b>Static</b>					
BV <sub>DSS</sub>	-80	-	-	V	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA
V <sub>GS(th)</sub>	-2	-	-4		V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =-250μA
G <sub>FS</sub>	-	32.5	-	S	V <sub>DS</sub> = -10V, I <sub>D</sub> =-20A
I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
I <sub>DSS</sub>	-	-	-1	μA	V <sub>DS</sub> = -64V, V <sub>GS</sub> = 0V
	-	-	-10		V <sub>DS</sub> = -64V, V <sub>GS</sub> = 0V, T <sub>j</sub> =125°C
*R <sub>DS(ON)</sub>	-	13.5	18.5	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> =-50A
<b>Dynamic</b>					
*Q <sub>g</sub>	-	91.8	-	nC	I <sub>D</sub> =-50A, V <sub>DS</sub> =-40V, V <sub>GS</sub> =-10V
*Q <sub>gs</sub>	-	18.4	-		
*Q <sub>gd</sub>	-	32.7	-		
*t <sub>d(ON)</sub>	-	35	-	ns	V <sub>DS</sub> =-40V, I <sub>D</sub> =-50A, V <sub>GS</sub> =-10V, R <sub>G</sub> =1Ω
*t <sub>r</sub>	-	28.8	-		
*t <sub>d(OFF)</sub>	-	74.6	-		
*t <sub>f</sub>	-	20.8	-		
C <sub>iss</sub>	-	5013	-	pF	V <sub>GS</sub> =0V, V <sub>DS</sub> =-40V, f=1MHz
C <sub>oss</sub>	-	386	-		
C <sub>rss</sub>	-	125	-		
R <sub>g</sub>	-	2.4	-	Ω	f=1MHz
<b>Source-Drain Diode</b>					
*I <sub>S</sub>	-	-	-63	A	
*I <sub>SM</sub>	-	-	-214		
*V <sub>SD</sub>	-	-0.88	-1.2	V	I <sub>S</sub> =-30A, V <sub>GS</sub> =0V
*t <sub>rr</sub>	-	30	-	ns	I <sub>F</sub> =-30A, V <sub>GS</sub> =0V, dI <sub>F</sub> /dt=100A/μs
*Q <sub>rr</sub>	-	37.7	-	nC	

\*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

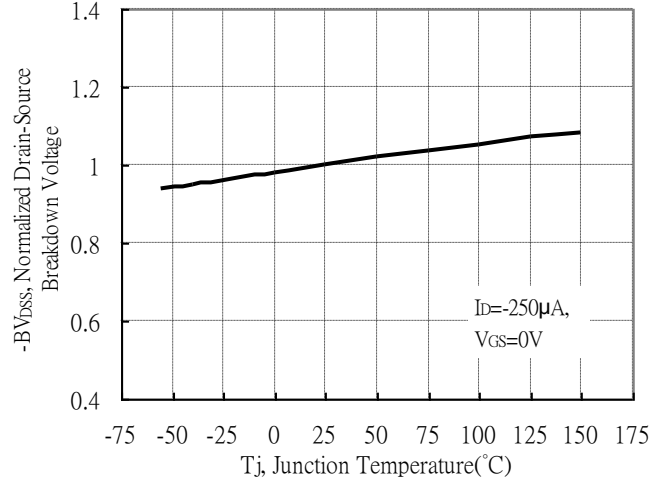


**Typical Characteristics**

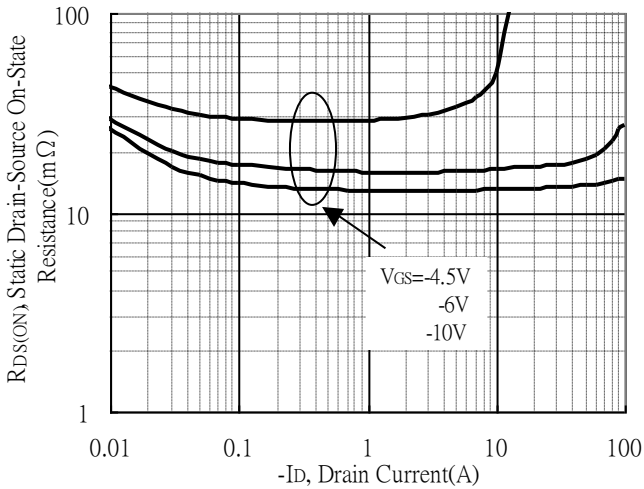
Typical Output Characteristics



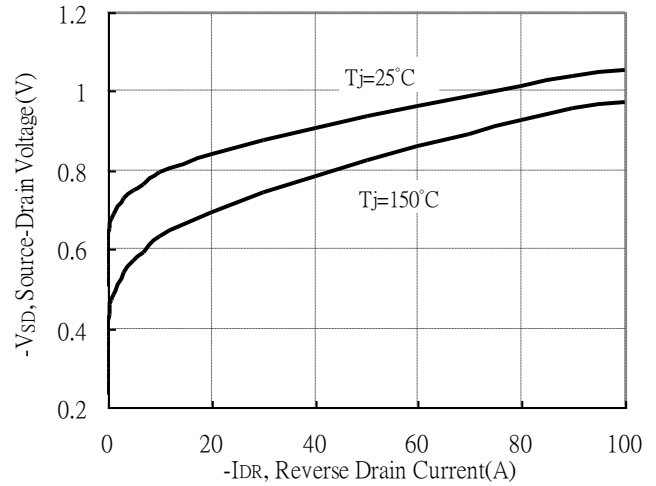
Breakdown Voltage vs Junction Temperature



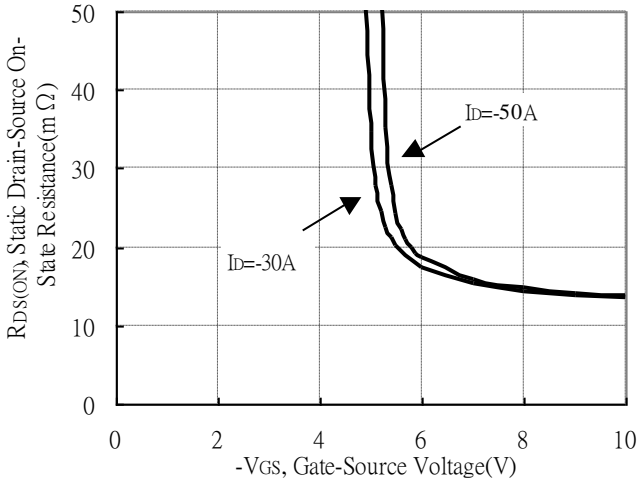
Static Drain-Source On-State resistance vs Drain Current



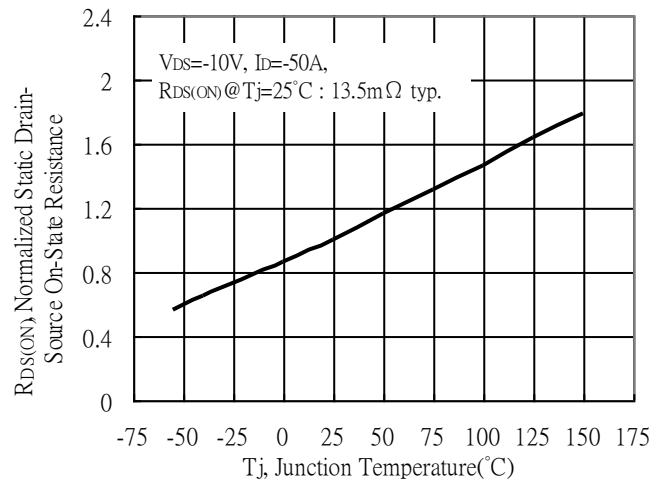
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

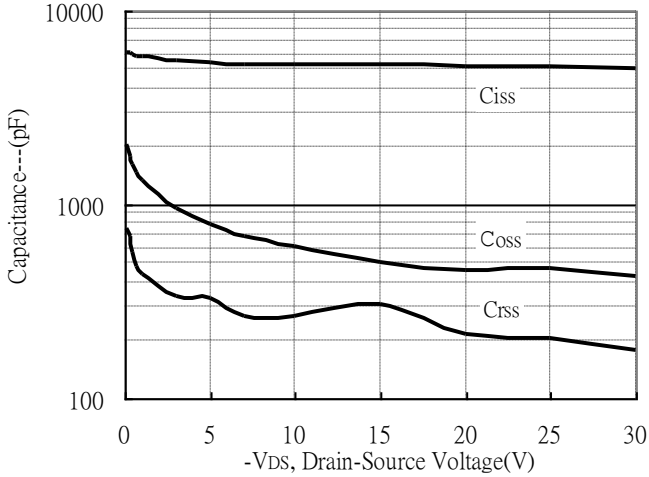


Drain-Source On-State Resistance vs Junction Temperature

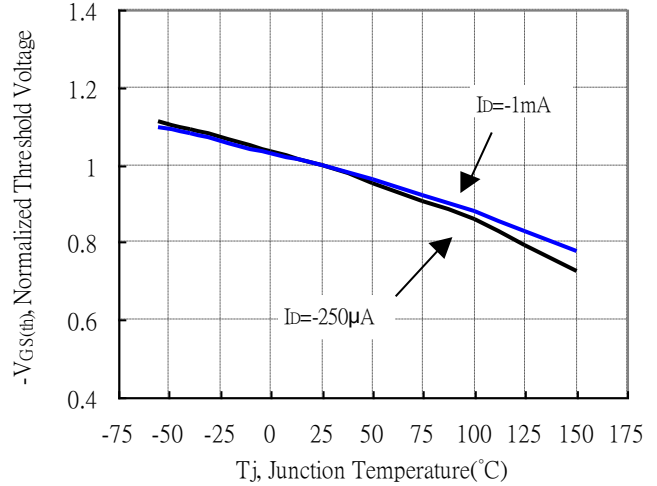


## Typical Characteristics(Cont.)

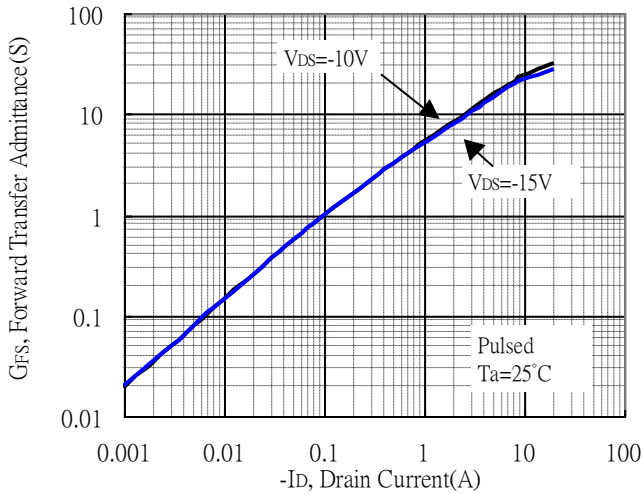
Capacitance vs Drain-to-Source Voltage



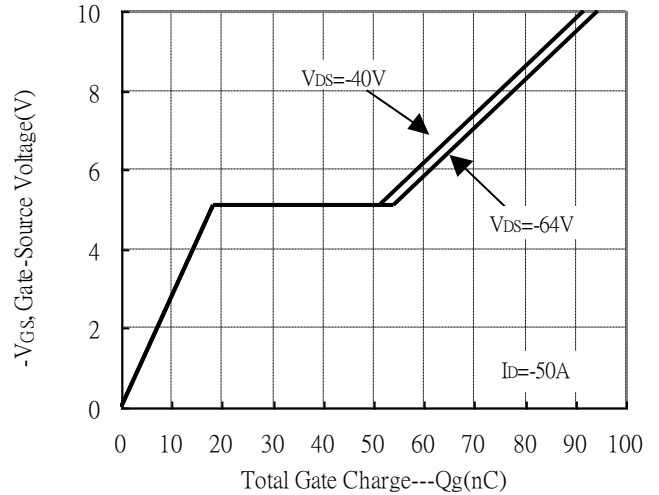
Threshold Voltage vs Junction Temperature



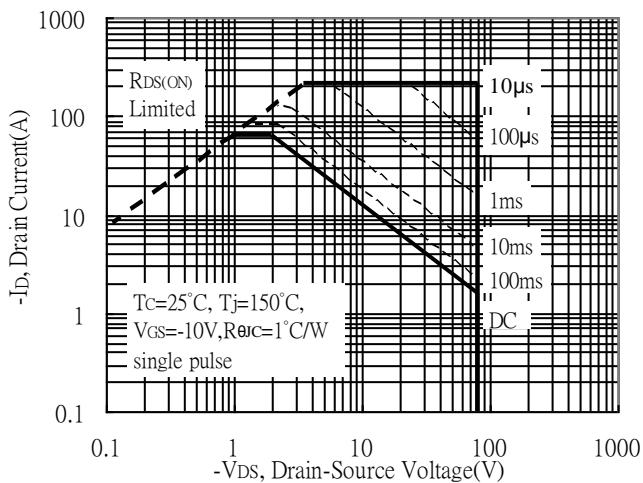
Forward Transfer Admittance vs Drain Current



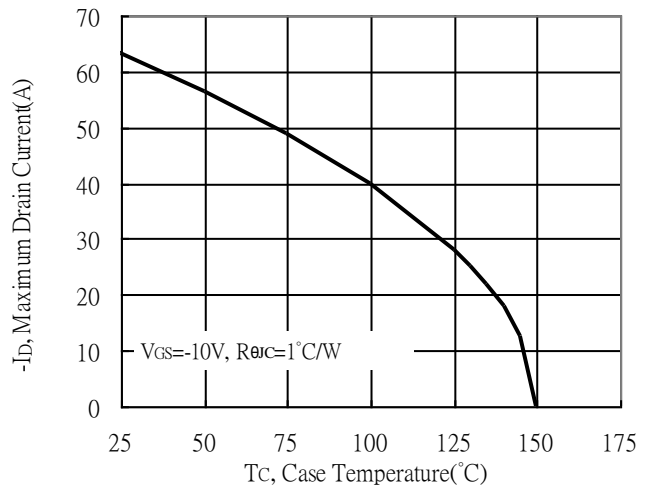
Gate Charge Characteristics



Maximum Safe Operating Area

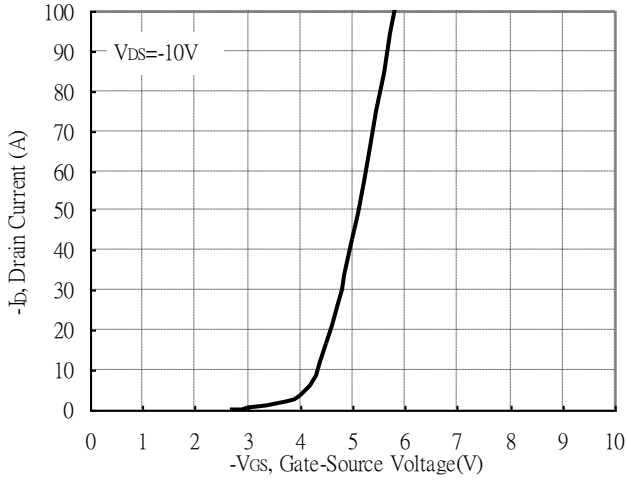


Maximum Drain Current vs Case Temperature

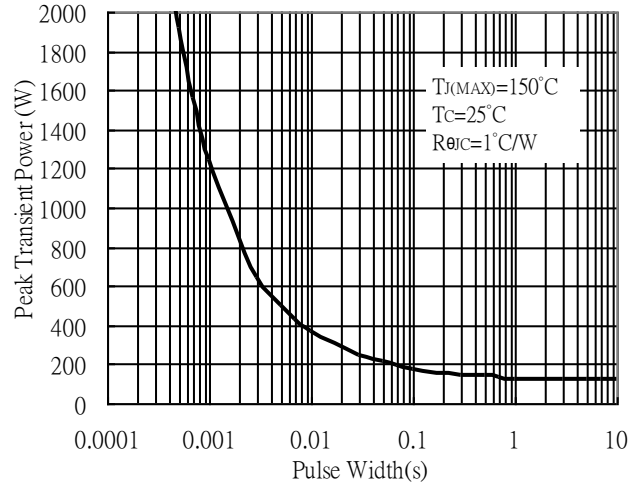


**Typical Characteristics(Cont.)**

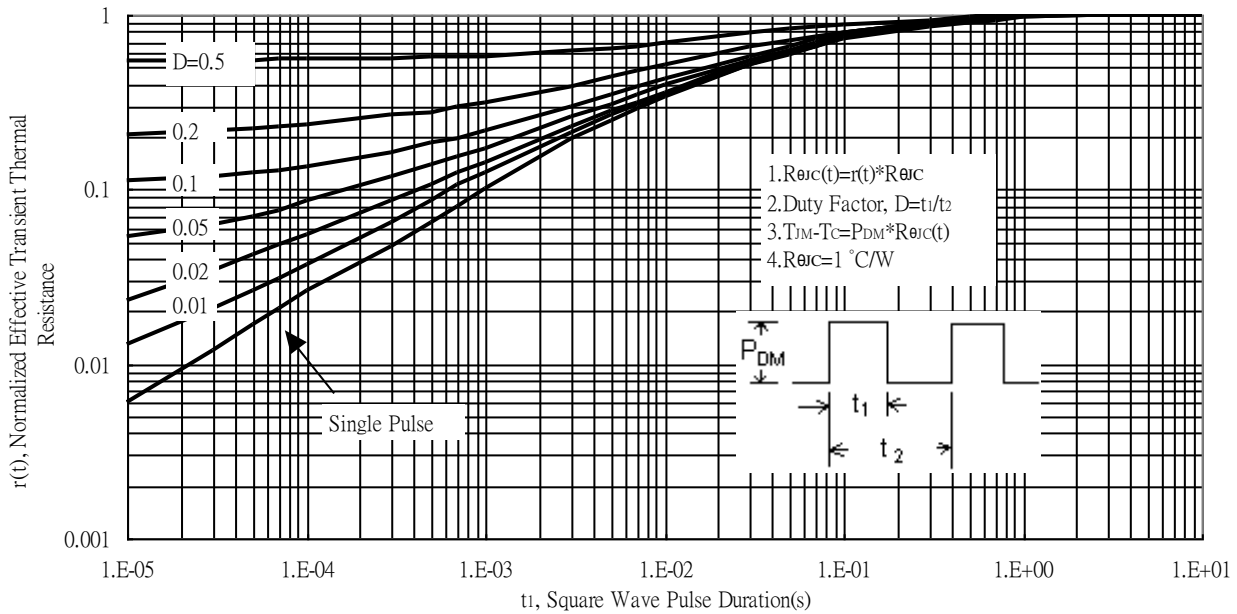
Typical Transfer Characteristics



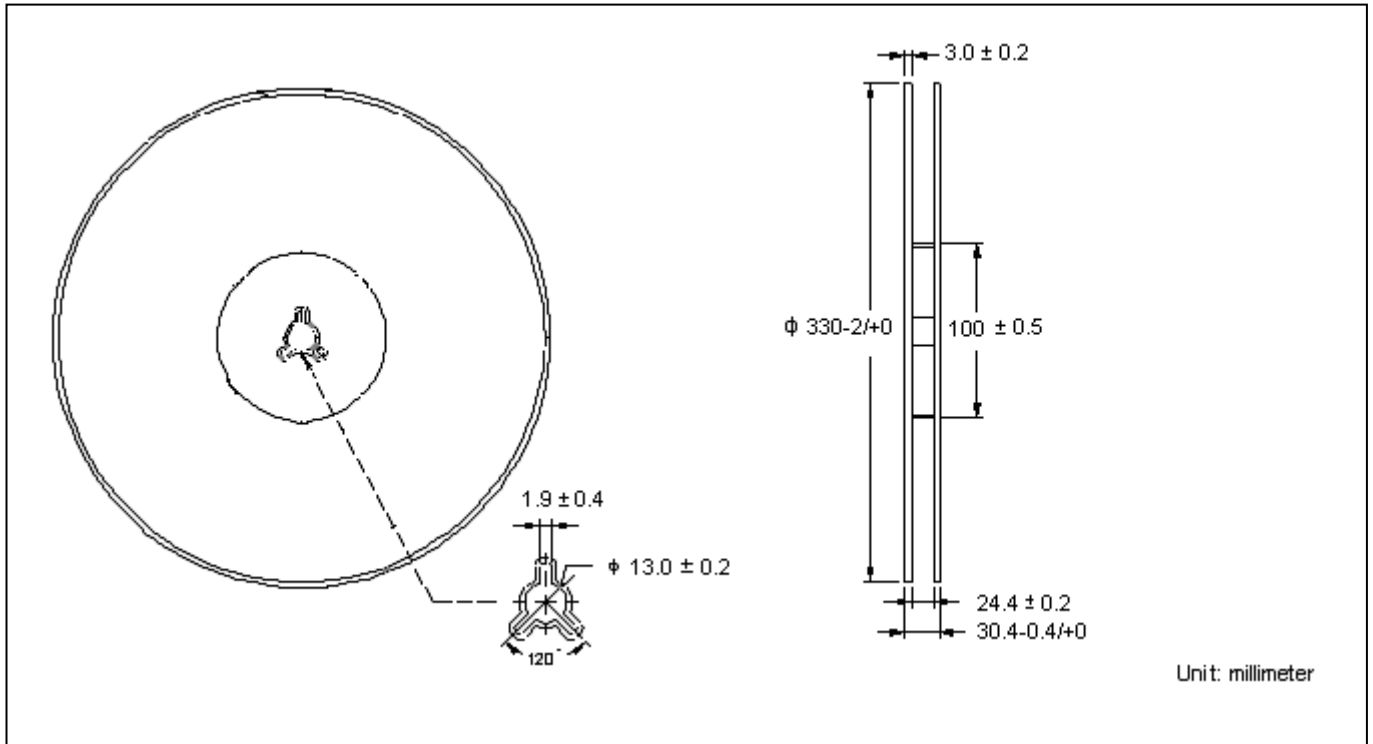
Single Pulse Maximum Power Dissipation



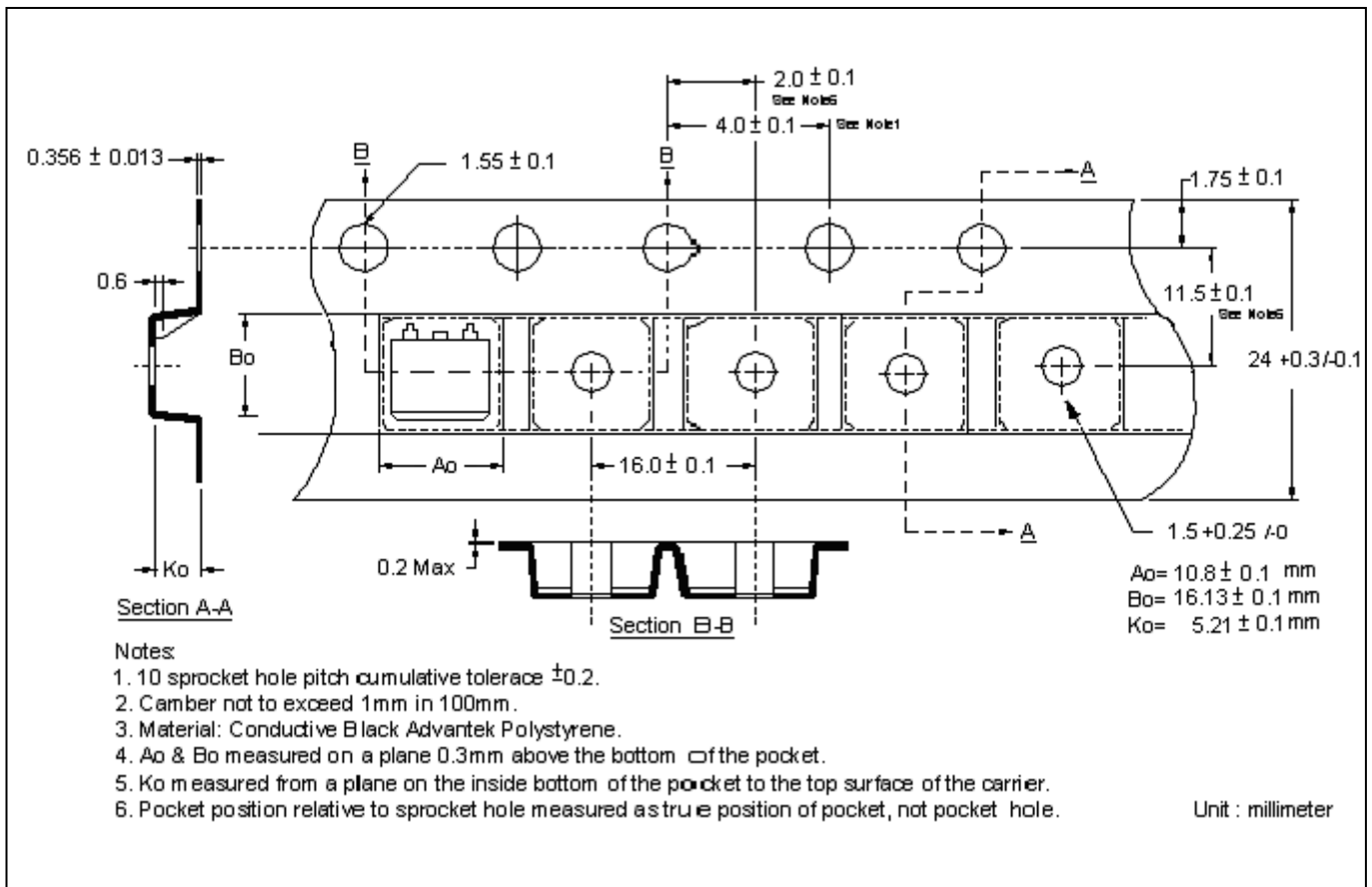
Transient Thermal Response Curves



**Reel Dimension**



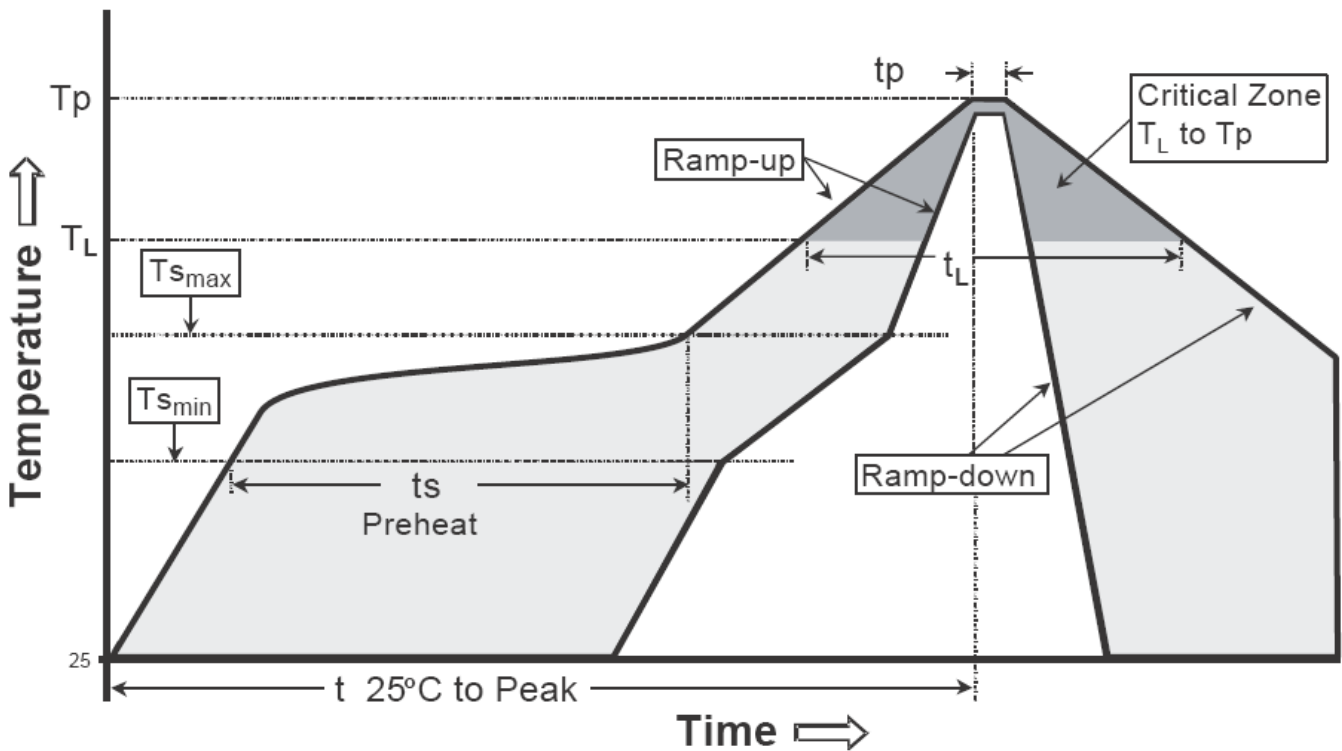
**Carrier Tape Dimension**



**Recommended wave soldering condition**

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

**Recommended temperature profile for IR reflow**

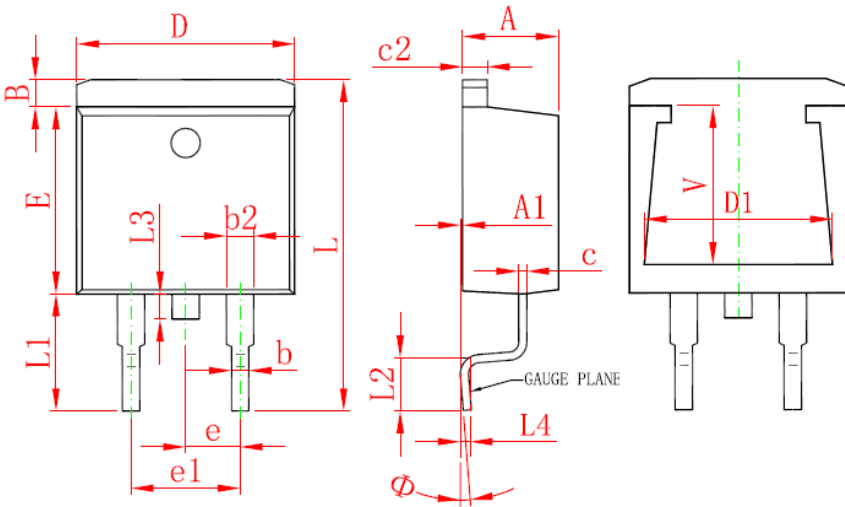


Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (TL)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.



**TO-263 Dimension**



The diagram shows three views of the TO-263 package: a top view, a side view, and a bottom view. Dimensions are labeled with letters and numbers. The top view shows dimensions D, B, E, L, L3, b2, b, e, and e1. The side view shows dimensions A, c2, A1, c, L2, L4, and a gauge plane. The bottom view shows dimensions V and D1. A marking diagram shows a rectangular package with three leads labeled 1, 2, and 3. The marking includes a device code 'E012 P08' and a date code represented by four squares.

**Marking :**

Device Code → E012  
 P08  
 Date Code → □□□□

1 2 3

Style : Pin 1.Gate 2.Drain  
 3.Source

**3-Lead Plastic Surface Mounted Package  
 CYStek Package Code : F3**

Date Code : (From left to right)  
 First Code : Year code, the last digit of Christian year. For example, 2014→4, 2015→, 2016→6, ..., etc.  
 Second Code : Month code, Jan→A, Feb→B, Mar→C, Apr→D, May→E, Jun→F, Jul→G, Aug→H, Sep→J,  
 Oct→K, Nov→L, Dec→M  
 Third and fourth codes : production serial number, 01~99

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184	e	2.540 TYP		0.100 TYP	
A1	0.000	0.150	0.000	0.006	e1	4.980	5.180	0.196	0.204
B	1.120	1.420	0.044	0.056	L	14.940	15.500	0.588	0.610
b	0.710	0.910	0.028	0.036	L1	4.950	5.450	0.195	0.215
b1	1.170	1.370	0.046	0.054	L2	2.340	2.740	0.092	0.108
c	0.381	0.530	0.015	0.021	L3	1.300	1.700	0.051	0.067
c1	1.170	1.370	0.046	0.054	L4	0.250 BSC		0.010 BSC	
D	10.010	10.310	0.394	0.406	Φ	0°	8°	0°	8°
D1	7.562	8.562	0.245	0.337	V	5.880	6.880	0.231	0.271
E	8.500	8.900	0.335	0.350					

Notes : 1.Controlling dimension : millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material :

- Lead : Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

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